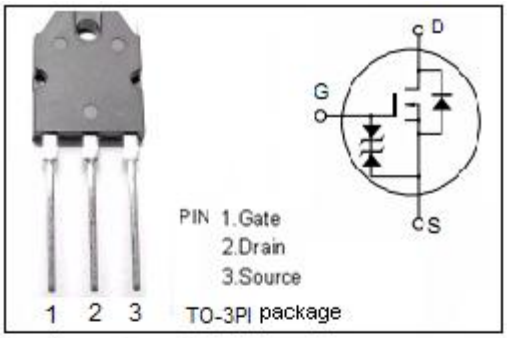
isc N-Channel MOSFET Transistor 2SK682

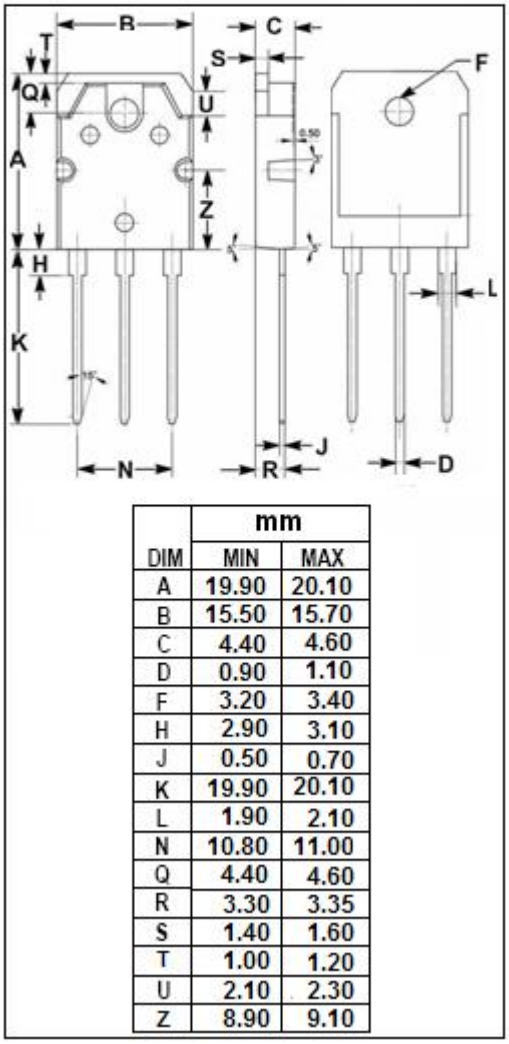


DESCRIPTION

- Drain Current $-I_D$=12A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=450V(Min)
- Fast Switching Speed

APPLICATIONS

- low on–resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switchingregulator, DC–DC convertor



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	450	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	12	A
P_{tot}	Total Dissipation@TC=25℃	100	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	450			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D= 1mA	2.0		4.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D=6A		0.4	0.55	Ω
V_{SD}	Diode Forward Voltage	I_F= 12A; V_{GS}=0		1.0		V
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±16V; V_{DS}= 0			±10	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=360V; V_{GS}= 0			250	uA
tr	Rise time	V_{GS}=10V;I_D=6A;R_L=5Ω		85		ns
ton	Turn-on time			110		ns
tf	Fall time			85		ns
toff	Turn-off time			230		ns

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